



**2N6036**  
**2N6039**

## COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

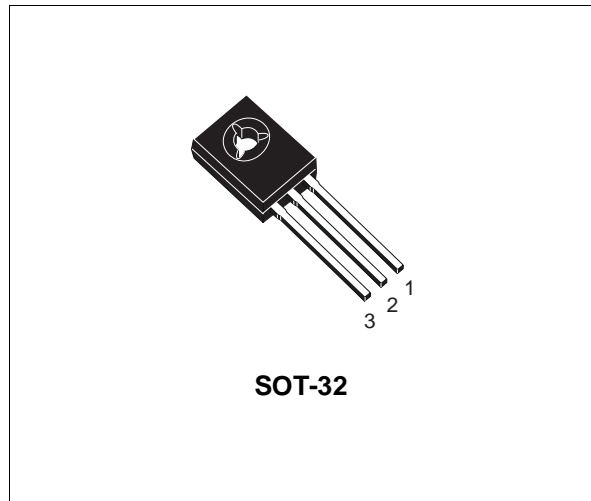
- 2N6036 IS A STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP - NPN DEVICES
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

### APPLICATIONS

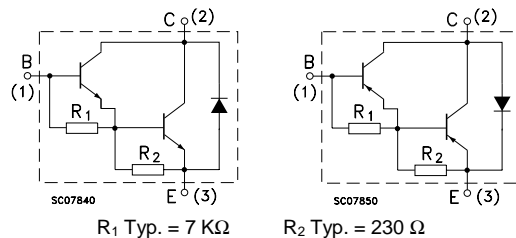
- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIER

### DESCRIPTION

The 2N6036 and 2N6039 are complementary silicon power Darlington transistors mounted in Jedec SOT-32 plastic package.



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		PNP	2N6036	
		NPN	2N6039	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )		80	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )		80	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )		5	V
$I_C$	Collector Current		4	A
$I_{CM}$	Collector Peak Current		8	A
$I_B$	Base Current		0.1	A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ\text{C}$		40	W
$T_{stg}$	Storage Temperature		-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature		150	$^\circ\text{C}$

For PNP types voltage and current values are negative.

**THERMAL DATA**

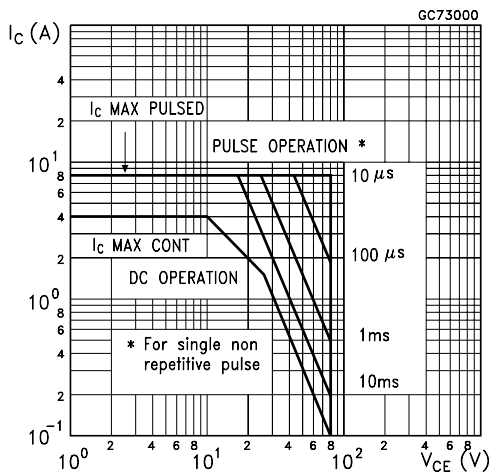
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.12	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	83.3	°C/W

**ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

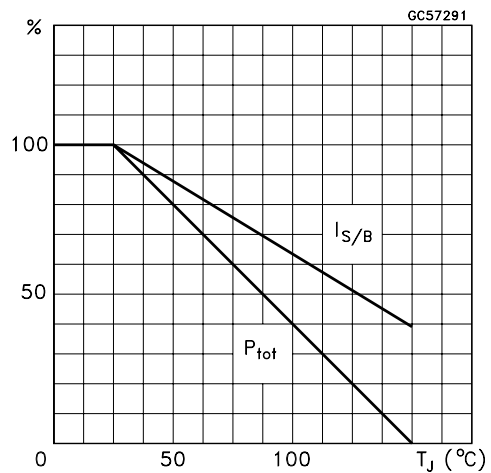
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CEX</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V)	V <sub>CE</sub> = rated V <sub>CEO</sub> V <sub>CE</sub> = rated V <sub>CEO</sub> T <sub>C</sub> = 125 °C			0.1 0.5	mA mA
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CE</sub> = rated V <sub>CBO</sub>			0.1	mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = rated V <sub>CEO</sub>			0.1	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA	80			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 A I <sub>B</sub> = 8 mA I <sub>C</sub> = 4 A I <sub>B</sub> = 40 mA			2 3	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4 A I <sub>B</sub> = 40 mA			4	V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 2 A V <sub>CE</sub> = 3 V			2.8	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 3 V I <sub>C</sub> = 2 A V <sub>CE</sub> = 3 V I <sub>C</sub> = 4 A V <sub>CE</sub> = 3 V	500 750 100		15000	
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 0.75 A V <sub>CE</sub> = 10 V f = 1KHz	25			
C <sub>CBO</sub>	Collector Base Capacitance	I <sub>E</sub> = 0 V <sub>CB</sub> = 10 V f = 1MHz for <b>NPN types</b> for <b>PNP types</b>			100 200	pF pF

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

**Safe Operating Area**



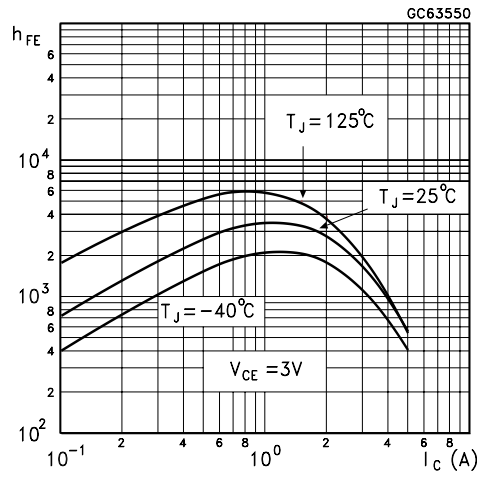
**Derating Curve**



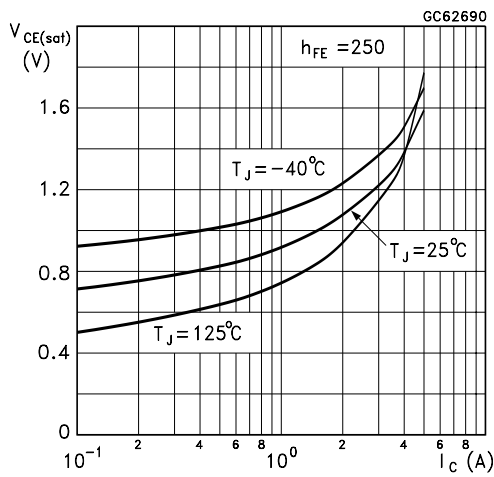
DC Current Gain (NPN type)



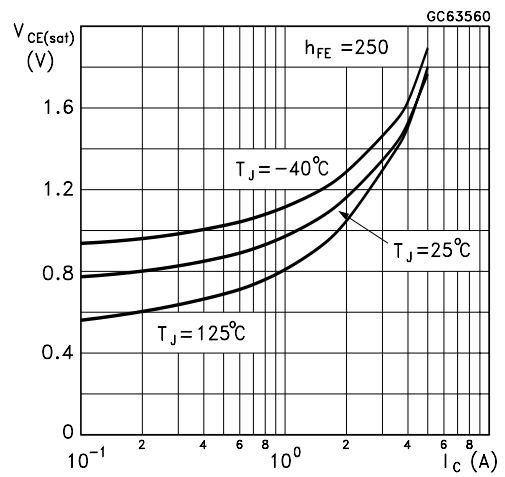
DC Current Gain (PNP type)



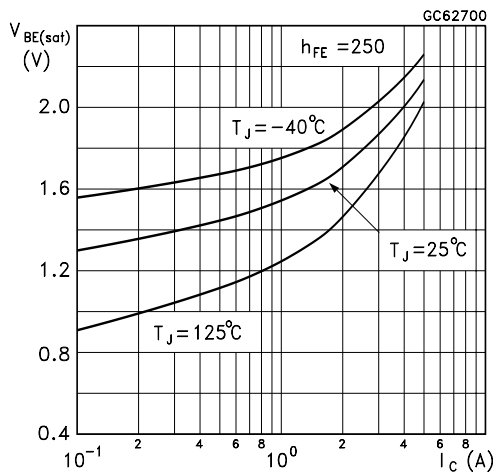
Collector Emitter Saturation Voltage (NPN type)



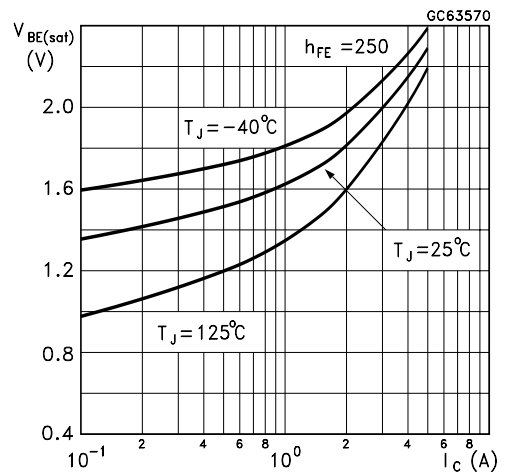
Collector Emitter Saturation Voltage (PNP type)



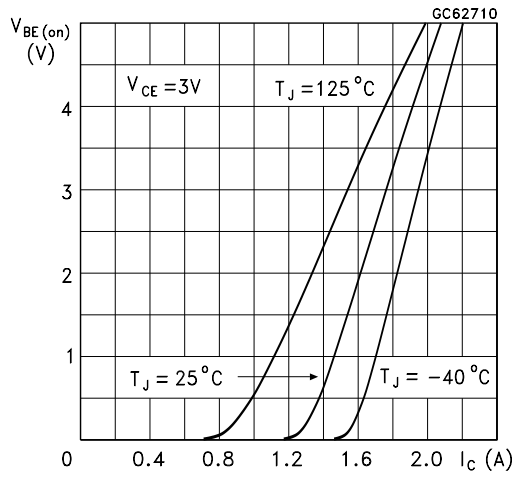
Base Emitter Saturation Voltage (NPN type)



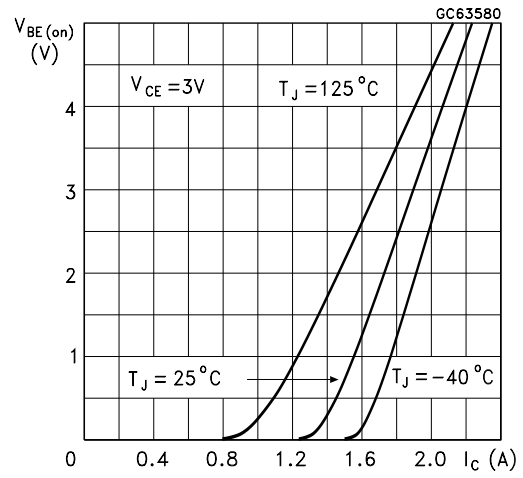
Base Emitter Saturation Voltage (PNP type)



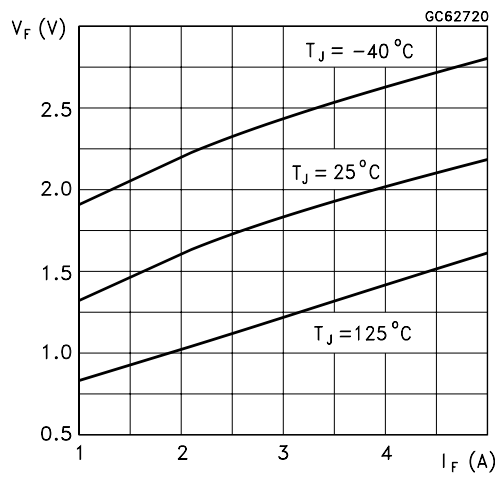
Base-Emitter On Voltage (NPN type)



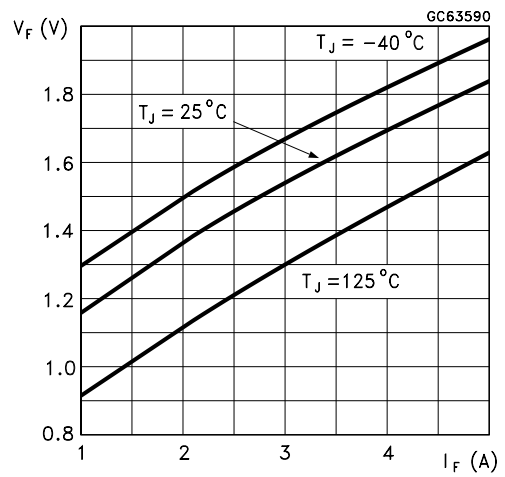
Base-Emitter On Voltage (PNP type)



Freewheel Diode Forward Voltage (NPN type)

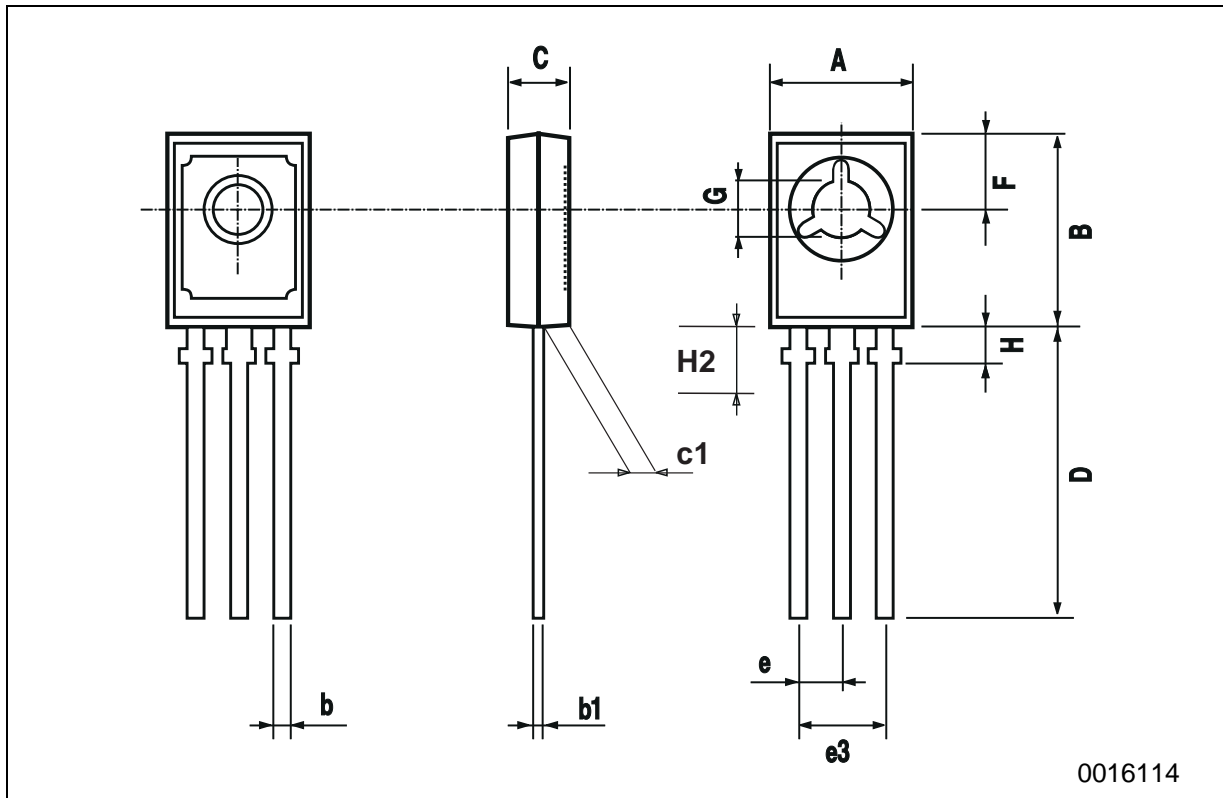


Freewheel Diode Forward Voltage (PNP type)



## SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
C	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
e		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
H			2.54			0.100



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